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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of

Ryota Nanjo et al

Serial No.: 10/084,367

Group Art Unit: Not Yet Assigned

Filed: February 28, 2002

Examiner: Not Yet Assigned

For: SEMICONDUCTOR DEVICE AND ITS MANUFACTURE

**INFORMATION DISCLOSURE STATEMENT**  
**PURSUANT TO 37 CFR 1.97(b)**

Commissioner for Patents  
Washington, D.C. 20231

April 25, 2002

Sir:

The attention of the Patent and Trademark Office is hereby directed to the documents listed on the attached Form PTO-1449. One copy of each of these documents is attached.

No fee or certification is required in connection with this Information Disclosure Statement, since it is being submitted prior to the issuance of a first official action on the merits or expiration of the three month period following filing of the above-captioned application.

The above information is presented so that the Patent and Trademark Office can, in the first instance, determine any materiality thereof to the claimed invention. See 37 CFR 1.104(a) and 1.106(b) concerning the PTO duty to consider and use any such information. It is respectfully requested that the information be expressly considered during the prosecution of this application, and that the documents cited in the attached Form PTO-1449 be made of record therein and appear on the first page of any patent to issue therefrom.

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Serial No.: 10/084,367

The Commissioner is authorized to charge our Deposit Account No. 01-2340 for any fee which is deemed by the Patent and Trademark Office to be required to effect consideration of this statement.

Respectfully submitted,

ARMSTRONG, WESTERMAN & HATTORI, LLP

A handwritten signature in black ink, appearing to read "Donald W. Hanson", written over a horizontal line.

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Enclosures: PTO-1449, 11 references

<b>INFORMATION DISCLOSURE CITATION #3</b> PTO-1449 APR 25 2002 PATENT & TRADEMARK OFFICE	Atty. Docket No. 020200	Serial No. 10/084,367
	Applicant(s): Ryota Nanjo et al	
	Filing Date: February 28, 2002	Group Art Unit: <del>Not Yet Assigned</del> 2822

### U.S. PATENT DOCUMENTS

Examiner Initial	Document No.	Name	Date	Class	Subclass	Filing Date (If appropriate)
_____	AA	5,956,603	Talwar et al	9/21/99	438	520
_____	AB					

### FOREIGN PATENT DOCUMENTS

	Document No.	Date	Country	Translation (Yes or No)
_____	AF 2001-007220	1/12/01	JP	Yes, abstract
_____	AG 2000-269491	9/29/00	JP	Yes, abstract
_____	AH 2000-196037	7/14/00	JP	Yes, abstract
_____	AI 07-231044	8/29/95	JP	Yes, abstract
_____	AJ 06-053157	2/25/94	JP	Yes, abstract
_____	AK 05-067776	3/19/93	JP	Yes, abstract

### OTHER DOCUMENTS

_____	AL	"Activation and Deactivation of Laser Thermal Annealed Boron, Arsenic, Phosphorus and Antimony Ultra-Shallow Abrupt Junctions", Murto et al; TH-13; Ion Implantation Technology 2000
_____	AM	"Self-Aligned Nickel-Mono-Silicide Technology for High-Speed Deep Submicrometer Logic CMOS USI", Morimoto et al; Vol 42, No. 5, May 1995 IEEE, pp 915-923.
_____	AN	"70nm MOSFET with Ultra-shallow, Abrupt, and Super-doped S/D Extension Implemented by Laser Thermal Process (LTP); Bin Yu et al; 1999 IEEE
_____	AO	"Front End Processes"; International Technology Roadmap for Semiconductors 1999; pp 105-141

Examiner	Date Considered
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